

Silicon PNP Power Transistors

2SA1327

DESCRIPTION

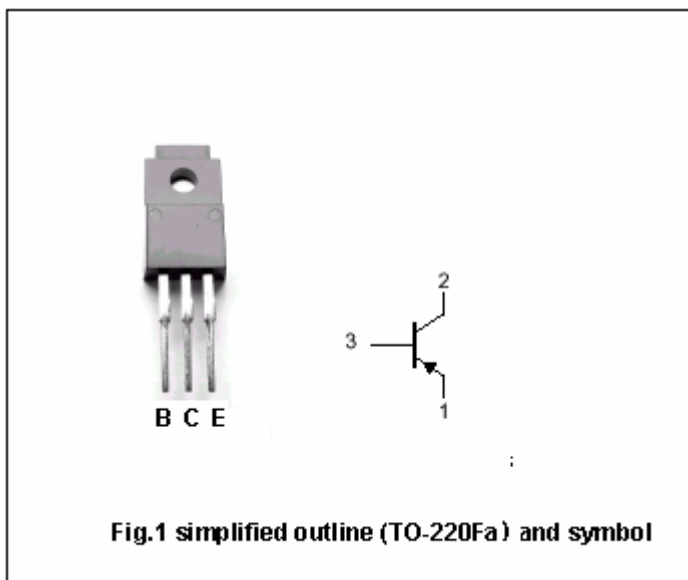
- With TO-220Fa package
- Low collector saturation voltage
- High current capacity

APPLICATIONS

- Strobe flash applications
- Audio power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-50	V
V _{CEO}	Collector-emitter voltage	Open base	-20	V
V _{EBO}	Emitter-base voltage	Open collector	-8	V
I _C	Collector current		-10	A
I _{CM}	Collector current-peak		-20	A
I _B	Base current		-2	A
P _C	Collector power dissipation	T _C =25	20	W
		T _a =25	2	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-20			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-8A; I _B =-0.4A			-0.5	V
V _{BE}	Base-emitter on voltage	I _C =-8A; V _{CE} =-2V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-8V; I _C =0			-1.0	μA
h _{FE-1}	DC current gain	I _C =-1A; V _{CE} =-2V	100		320	
h _{FE-2}	DC current gain	I _C =-8A; V _{CE} =-2V	70			
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		400		pF
f _T	Transition frequency	I _C =-1A; V _{CE} =-2V		45		MHz

◆ h_{FE-1} Classifications

O	Y
100-200	160-320

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PACKAGE OUTLINE

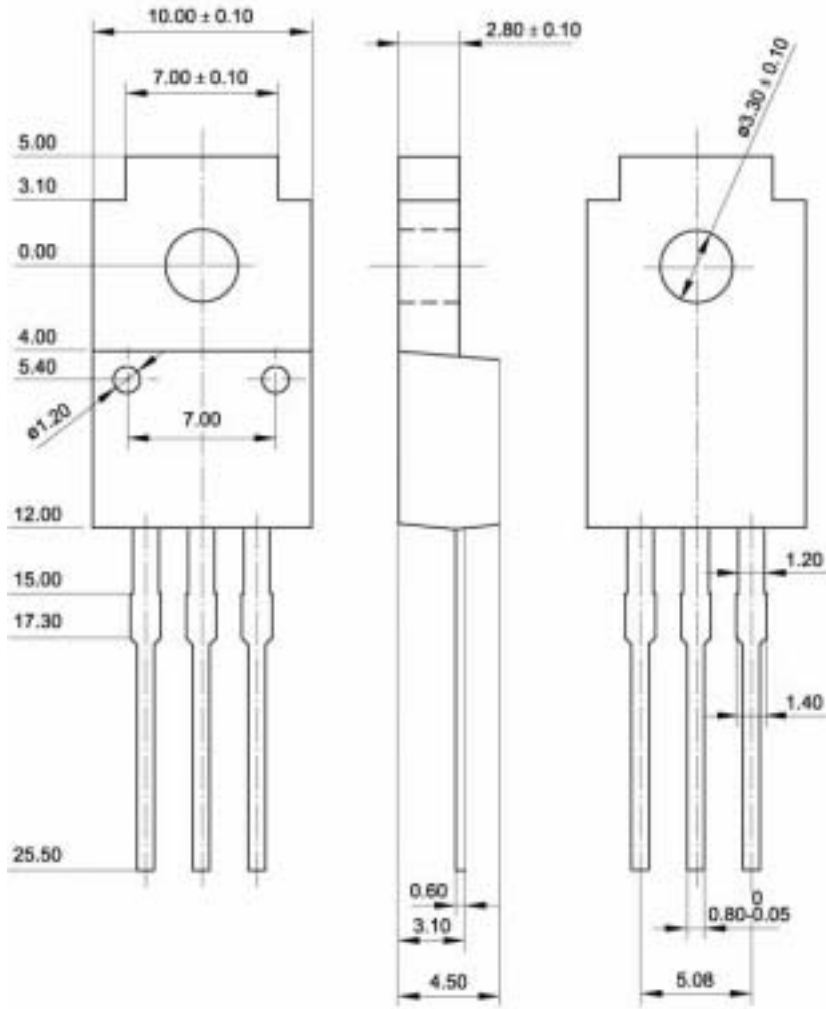


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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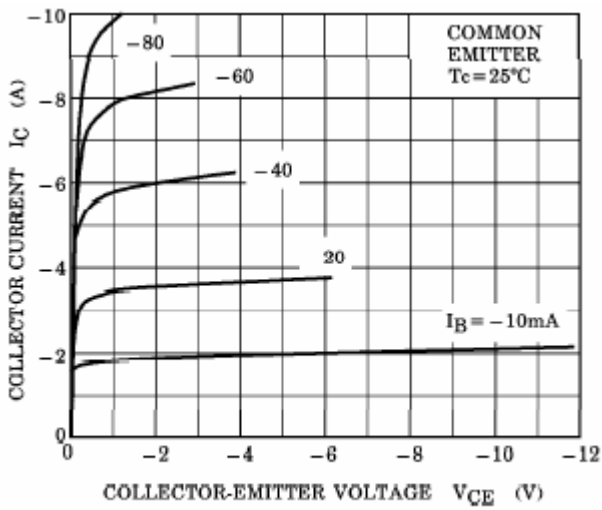


Fig.3 Static Characteristic

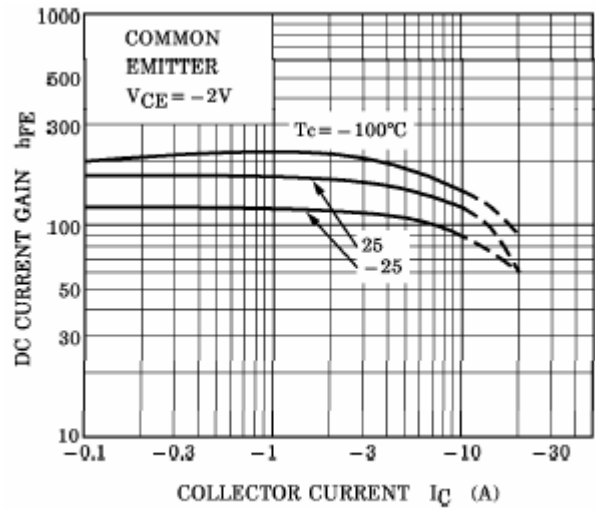


Fig.4 DC current Gain

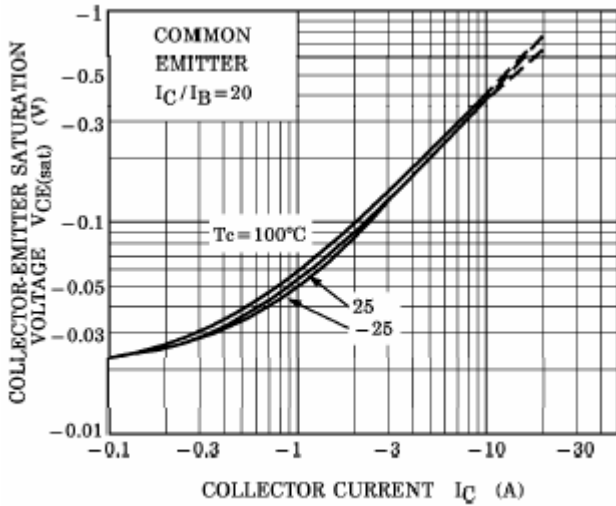


Fig.5 Collector-Emitter Saturation Voltage

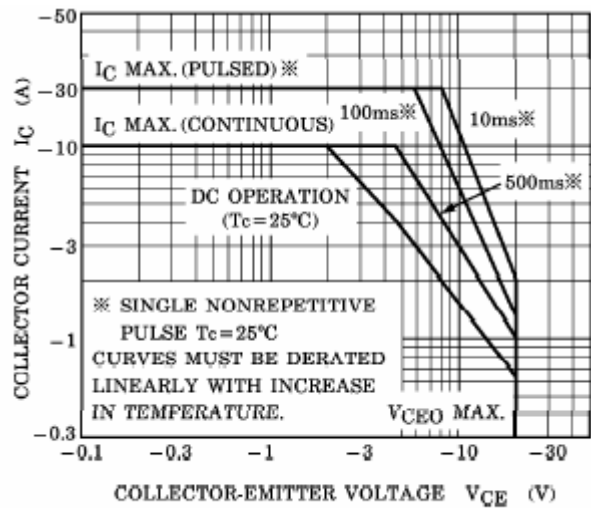


Fig.6 Safe Operating Area